NEC

MOS INTEGRATED CIRCUIT

μPD4264805, 42S65805, 4265805

64 M-BIT DYNAMIC RAM
8 M-WORD BY 8-BIT, EDO

Description

The μPD4264805, 42S65805, 4265805 are 8,388,608 words by 8 bits CMOS dynamic RAMs with optional EDO.
EDO is a kind of the page mode and is useful for the read operation.
Besides, the μPD42S65805 can execute $\overline{\text{CAS}}$ before $\overline{\text{RAS}}$ self refresh.
These are packaged in 32-pin plastic TSOP (II) and 32-pin plastic SOJ.

Features

- EDO (Hyper page mode)
- 8,388,608 words by 8 bits organization
- Single +3.3 V ±0.3 V power supply
- Fast access and cycle time

★

Part number	Power consumption Active (MAX.)	Access time (MAX.)	R/W cycle time (MIN.)	EDO (Hyper page mode) cycle time (MIN.)
μPD4264805-A50	378 mW	50 ns	84 ns	20 ns
μPD42S65805-A50, 4265805-A50	486 mW			
μPD4264805-A60	342 mW	60 ns	104 ns	25 ns
μPD42S65805-A60, 4265805-A60	414 mW			

★ • The μPD42S65805 can execute $\overline{\text{CAS}}$ before $\overline{\text{RAS}}$ self refresh.

Part number	Refresh cycle	Refresh	Power consumption at standby (MAX.)
μPD42S65805	4,096 cycles/128 ms	$\overline{\text{RAS}}$ only refresh, Normal read/write, $\overline{\text{CAS}}$ before $\overline{\text{RAS}}$ self refresh, $\overline{\text{CAS}}$ before $\overline{\text{RAS}}$ refresh, Hidden refresh	0.72 mW (CMOS level input)
μPD4264805	8,192 cycles/64 ms	$\overline{\text{RAS}}$ only refresh, Normal read/write	1.8 mW (CMOS level input)
	4,096 cycles/64 ms	$\overline{\text{CAS}}$ before $\overline{\text{RAS}}$ refresh, Hidden refresh	
μPD4265805	4,096 cycles/64 ms	$\overline{\text{RAS}}$ only refresh, Normal read/write, $\overline{\text{CAS}}$ before $\overline{\text{RAS}}$ refresh, Hidden refresh	

The information in this document is subject to change without notice.

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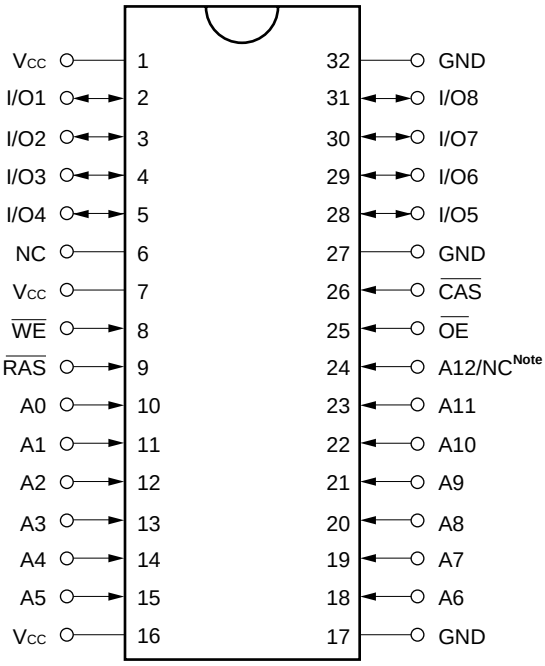
The mark ★ shows major revised points.

★ Ordering Information

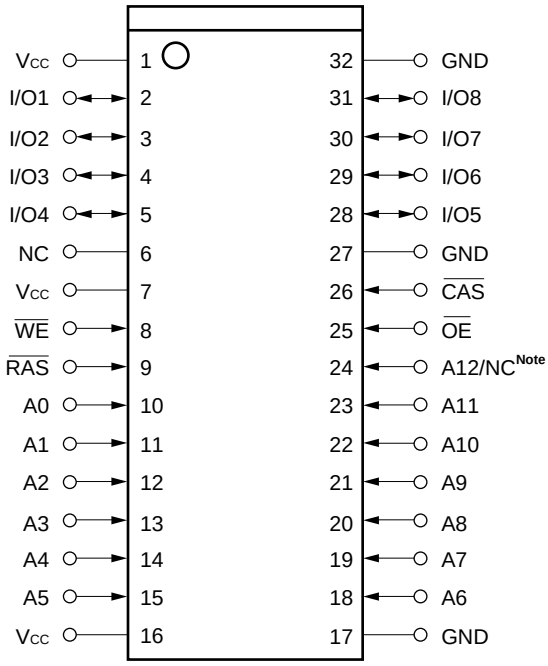
Part number	Access time (MAX.)	Package	Refresh
μPD42S65805G5-A50-7JD	50 ns	32-pin plastic TSOP (II) (400 mil)	$\overline{CAS}$ before $\overline{RAS}$ self refresh $\overline{CAS}$ before $\overline{RAS}$ refresh $\overline{RAS}$ only refresh Hidden refresh
μPD42S65805G5-A60-7JD	60 ns		
μPD42S65805LE-A50	50 ns	32-pin plastic SOJ (400 mil)	
μPD42S65805LE-A60	60 ns		
μPD4264805G5-A50-7JD	50 ns	32-pin plastic TSOP (II) (400 mil)	$\overline{CAS}$ before $\overline{RAS}$ refresh $\overline{RAS}$ only refresh Hidden refresh
μPD4264805G5-A60-7JD	60 ns		
μPD4265805G5-A50-7JD	50 ns		
μPD4265805G5-A60-7JD	60 ns		
μPD4264805LE-A50	50 ns	32-pin plastic SOJ (400 mil)	
μPD4264805LE-A60	60 ns		
μPD4265805LE-A50	50 ns		
μPD4265805LE-A60	60 ns		

★ **Pin Configurations** (Marking Side)

32-pin Plastic TSOP (Ⅱ) (400 mil)
μPD4264805G5-7JD
μPD42S65805G5-7JD
μPD4265805G5-7JD



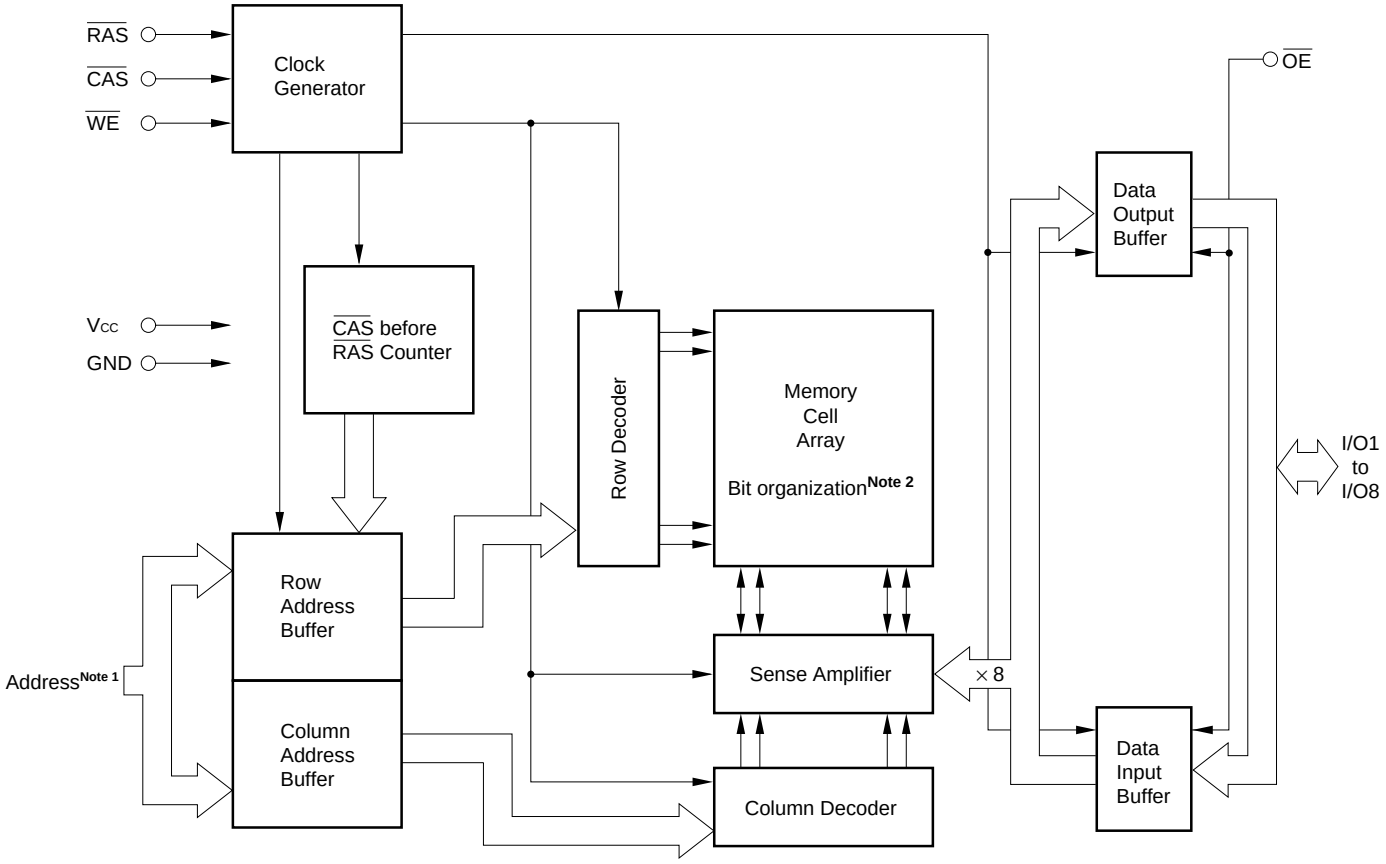
32-pin Plastic SOJ (400 mil)
μPD4264805LE
μPD42S65805LE
μPD4265805LE



Note A12 ... μPD4264805
NC ... μPD42S65805, 4265805

A0 to A12 : Address Inputs
I/O1 to I/O8 : Data Inputs/Outputs
$\overline{RAS}$: Row Address Strobe
$\overline{CAS}$: Column Address Strobe
$\overline{WE}$: Write Enable
$\overline{OE}$: Output Enable
VCC : Power Supply
GND : Ground
NC : No Connection

Block Diagram



★ **Notes 1.**

Part number	Row address	Column address
μPD4264805	A0 – A12	A0 – A9
μPD42S65805, 4265805	A0 – A11	A0 – A10

2. 4,096 x 2,048 x 8

Input/Output Pin Functions

The μPD4264805, 42S65805, 4265805 have input pins $\overline{RAS}$, $\overline{CAS}$, $\overline{WE}$, $\overline{OE}$, Address[Note] and input/output pins I/O1 to I/O8.

Pin name	Input/Output	Function
$\overline{RAS}$ (Row address strobe)	Input	$\overline{RAS}$ activates the sense amplifier by latching a row address and selecting a corresponding word line. It refreshes memory cell array of one line selected by the row address. It also selects the following function. • $\overline{CAS}$ before $\overline{RAS}$ self refresh, $\overline{CAS}$ before $\overline{RAS}$ refresh
$\overline{CAS}$ (Column address strobe)	Input	$\overline{CAS}$ activates data input/output circuit by latching column address and selecting a digit line connected with the sense amplifier.
A0 to A×[Note] (Address inputs)	Input	Address bus. Input total 23-bit of address signal, upper bits and lower bits[Note] in sequence (address multiplex method). Therefore, one word is selected from 8,388,608-word by 8-bit memory cell array. In actual operation, latch row address by specifying row address and activating $\overline{RAS}$. Then, switch the address bus to column address and activate $\overline{CAS}$. Each address is taken into the device when $\overline{RAS}$ and $\overline{CAS}$ are activated. Therefore, the address input setup time (t_{ASR}, t_{ASC}) and hold time (t_{RAH}, t_{CAH}) are specified for the activation of $\overline{RAS}$ and $\overline{CAS}$.
$\overline{WE}$ (Write enable)	Input	Write control signal. Write operation is executed by activating $\overline{RAS}$, $\overline{CAS}$ and $\overline{WE}$.
$\overline{OE}$ (Output enable)	Input	Read control signal. Read operation can be executed by activating $\overline{RAS}$, $\overline{CAS}$ and $\overline{OE}$. If $\overline{WE}$ is activated during read operation, $\overline{OE}$ is to be ineffective in the device. Therefore, read operation cannot be executed.
I/O1 to I/O8 (Data inputs/outputs)	Input/Output	8-bit data bus. I/O1 to I/O8 are used to input/output data.

★ **Note**

Part number	Address inputs	Upper bits	Lower bits
μPD4264805	A0 - A12	13	10
μPD42S65805, 4265805	A0 - A11	12	12

Hyper Page Mode (EDO)

The hyper page mode (EDO) is a kind of page mode with enhanced features. The two major features of the hyper page mode (EDO) are as follows.

1. Data output time is extended.

In the hyper page mode (EDO), the output data is held to the next $\overline{CAS}$ cycle's falling edge, instead of the rising edge. For this reason, valid data output time in the hyper page mode (EDO) is extended compared with the fast page mode (= data extend function). In the fast page mode, the data output time becomes shorter as the $\overline{CAS}$ cycle time becomes shorter. Therefore, in the hyper page mode (EDO), the timing margin in read cycle is larger than that of the fast page mode even if the $\overline{CAS}$ cycle time becomes shorter.

2. The $\overline{CAS}$ cycle time in the hyper page mode (EDO) is shorter than that in the fast page mode.

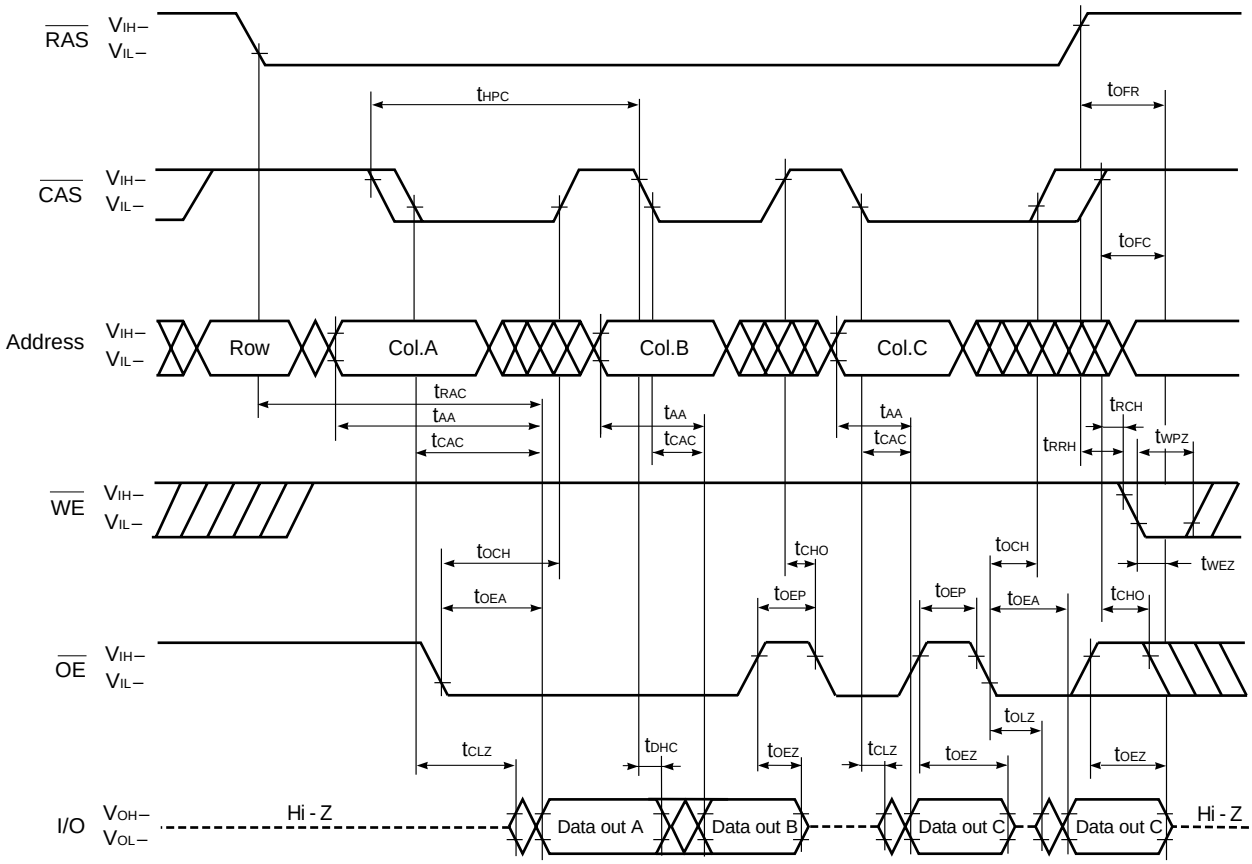
In the hyper page mode (EDO), due to the data extend function, the $\overline{CAS}$ cycle time can be shorter than in the fast page mode if the timing margin is the same.

Taking a device whose t_{RAC} is 60 ns as an example, the $\overline{CAS}$ cycle time in the fast page mode is 25 ns while that in the fast page mode is 40 ns.

In the hyper page mode (EDO) , read (data out) and write (data in) cycles can be executed repeatedly during one $\overline{RAS}$ cycle. The hyper page mode (EDO) allows both read and write operations during one cycle.

The following shows a part of the hyper page mode (EDO) read cycle. Specifications to be observed are described in the next page.

Hyper Page Mode (EDO) Read Cycle



Cautions when using the hyper page mode (EDO)

1. $\overline{CAS}$ access should be used to operate t_{HPC} at the MIN. value.

2. To make I/Os to Hi-Z in read cycle, it is necessary to control $\overline{RAS}$, $\overline{CAS}$, $\overline{WE}$, $\overline{OE}$ as follows. The effective specification depends on the state of each signal.

(1) Both $\overline{RAS}$ and $\overline{CAS}$ are inactive (at the end of read cycle)

$\overline{WE}$: inactive, $\overline{OE}$: active

t_{OFC} is effective when $\overline{RAS}$ is inactivated before $\overline{CAS}$ is inactivated.

t_{OFR} is effective when $\overline{CAS}$ is inactivated before $\overline{RAS}$ is inactivated.

The slower of t_{OFC} and t_{OFR} becomes effective.

(2) Both $\overline{RAS}$ and $\overline{CAS}$ are active or either $\overline{RAS}$ or $\overline{CAS}$ is active (in read cycle)

$\overline{WE}$, $\overline{OE}$: inactive ····· t_{OEZ} is effective.

Both $\overline{RAS}$ and $\overline{CAS}$ are inactive or $\overline{RAS}$ is active and $\overline{CAS}$ is inactive (at the end of read cycle)

$\overline{WE}$, $\overline{OE}$: active and either t_{RRH} or t_{RCH} must be met ····· t_{WEZ} and t_{WPZ} are effective.

The faster of t_{OEZ} and t_{WEZ} becomes effective.

The faster of (1) and (2) becomes effective.

3. In read cycle, the effective specification depends on the state of $\overline{CAS}$ signal when controlling data output with the $\overline{OE}$ signal.

(1) $\overline{CAS}$: inactive, $\overline{OE}$: active ····· t_{OHO} is effective.

(2) $\overline{CAS}$, $\overline{OE}$: active ····· t_{OCH} is effective.

Electrical Specifications

- All voltages are referenced to GND.
- After power up ($V_{CC} \geq V_{CC\ (MIN.)}$), wait more than 100 μs ($\overline{RAS}$, $\overline{CAS}$ inactive) and then, execute eight $\overline{CAS}$ before $\overline{RAS}$ or $\overline{RAS}$ only refresh cycles as dummy cycles to initialize internal circuit.

Absolute Maximum Ratings

Parameter	Symbol	Condition	Rating	Unit
Voltage on any pin relative to GND	V_T		–0.5 to +4.6	V
Supply voltage	V_{CC}		–0.5 to +4.6	V
Output current	I_O		50	mA
Power dissipation	P_D		1	W
Operating ambient temperature	T_A		0 to +70	˚C
Storage temperature	T_{stg}		–55 to +125	˚C

Caution Exposing the device to stress above those listed in Absolute Maximum Ratings could cause permanent damage. The device is not meant to be operated under conditions outside the limits described in the operational section of this specification. Exposure to Absolute Maximum Rating conditions for extended periods may affect device reliability.

Recommended Operating Conditions

Parameter	Symbol	Condition	MIN.	TYP.	MAX.	Unit
Supply voltage	V_{CC}		3.0	3.3	3.6	V
High level input voltage	V_{IH}		2.0		V_{CC} + 0.3	V
Low level input voltage	V_{IL}		–0.3		+0.8	V
Operating ambient temperature	T_A		0		70	˚C

Capacitance (T_A = 25 ˚C, f = 1 MHz)

Parameter	Symbol	Test condition	MIN.	TYP.	MAX.	Unit
Input capacitance	C_{I1}	Address			5	pF
	C_{I2}	$\overline{RAS}$, $\overline{CAS}$, $\overline{WE}$, $\overline{OE}$			7	
Data input/output capacitance	$C_{I/O}$	I/O			7	pF

★ **DC Characteristics (Recommended operating conditions unless otherwise noted)**

[μPD4264805]

Parameter	Symbol	Test condition		MIN.	MAX.	Unit	Notes
Operating current	I_{CC1}	$\overline{RAS}$, $\overline{CAS}$ cycling	t_{RAC} = 50 ns		105	mA	1, 2, 3
		$t_{RC} = t_{RC\ (MIN.)}$, I_O = 0 mA	t_{RAC} = 60 ns		95		
Standby current	I_{CC2}	$\overline{RAS}$, $\overline{CAS} \geq V_{IH\ (MIN.)}$, I_O = 0 mA			1.0	mA	
		$\overline{RAS}$, $\overline{CAS} \geq V_{CC}$ – 0.2 V, I_O = 0 mA			0.5		
$\overline{RAS}$ only refresh current	I_{CC3}	$\overline{RAS}$ cycling, $\overline{CAS} \geq V_{IH\ (MIN.)}$	t_{RAC} = 50 ns		105	mA	1, 2, 3 ,4
		$t_{RC} = t_{RC\ (MIN.)}$, I_O = 0 mA	t_{RAC} = 60 ns		95		
Operating current	I_{CC4}	$\overline{RAS} \leq V_{IL\ (MAX.)}$, $\overline{CAS}$ cycling	t_{RAC} = 50 ns		105	mA	1, 2, 5
(Hyper page mode (EDO))		$t_{HPC} = t_{HPC\ (MIN.)}$, I_O = 0 mA	t_{RAC} = 60 ns		95		
$\overline{CAS}$ before $\overline{RAS}$	I_{CC5}	$\overline{RAS}$ cycling	t_{RAC} = 50 ns		135	mA	1, 2
refresh current		$t_{RC} = t_{RC\ (MIN.)}$, I_O = 0 mA	t_{RAC} = 60 ns		115		
Input leakage current	$I_{I\ (L)}$	V_I = 0 to 3.6 V All other pins not under test = 0 V		–5	+5	μA	
Output leakage current	$I_{O\ (L)}$	V_O = 0 to 3.6 V Output is disabled (Hi-Z)		–5	+5	μA	
High level output voltage	V_{OH}	I_O = –2.0 mA		2.4		V	
Low level output voltage	V_{OL}	I_O = +2.0 mA			0.4	V	

[μPD42S65805, 4265805]

Parameter		Symbol	Test condition		MIN.	MAX.	Unit	Notes
Operating current		I_{CC1}	$\overline{RAS}$, $\overline{CAS}$ cycling	t_{RAC} = 50 ns		135	mA	1, 2, 3
			$t_{RC} = t_{RC\ (MIN.)}$, I_O = 0 mA	t_{RAC} = 60 ns		115		
Standby current	μPD42S65805	I_{CC2}	$\overline{RAS}$, $\overline{CAS} \geq V_{IH\ (MIN.)}$, I_O = 0 mA			1.0	mA	
			$\overline{RAS}$, $\overline{CAS} \geq V_{CC}$ – 0.2 V, I_O = 0 mA			0.2		
	μPD4265805		$\overline{RAS}$, $\overline{CAS} \geq V_{IH\ (MIN.)}$, I_O = 0 mA			1.0		
			$\overline{RAS}$, $\overline{CAS} \geq V_{CC}$ – 0.2 V, I_O = 0 mA			0.5		
$\overline{RAS}$ only refresh current		I_{CC3}	$\overline{RAS}$ cycling, $\overline{CAS} \geq V_{IH\ (MIN.)}$	t_{RAC} = 50 ns		135	mA	1, 2, 3 ,4
			$t_{RC} = t_{RC\ (MIN.)}$, I_O = 0 mA	t_{RAC} = 60 ns		115		
Operating current (Hyper page mode (EDO))		I_{CC4}	$\overline{RAS} \leq V_{IL\ (MAX.)}$, $\overline{CAS}$ cycling	t_{RAC} = 50 ns		105	mA	1, 2, 5
			$t_{HPC} = t_{HPC\ (MIN.)}$, I_O = 0 mA	t_{RAC} = 60 ns		95		
$\overline{CAS}$ before $\overline{RAS}$ refresh current		I_{CC5}	$\overline{RAS}$ cycling	t_{RAC} = 50 ns		135	mA	1, 2
			$t_{RC} = t_{RC\ (MIN.)}$, I_O = 0 mA	t_{RAC} = 60 ns		115		
$\overline{CAS}$ before $\overline{RAS}$ long refresh current (4,096 cycles/128 ms, only for the μPD42S65805)		I_{CC6}	$\overline{CAS}$ before $\overline{RAS}$ refresh: t_{RC} = 31.3 μs, $\overline{RAS}$, $\overline{CAS}$: V_{CC} – 0.2 V ≤ $V_{IH} \leq V_{IH\ (MAX.)}$, 0 V ≤ V_{IL} ≤ 0.2 V	$t_{RAS} \leq$ 300 ns		500	μA	1, 2
			Standby: $\overline{RAS}$, $\overline{CAS} \geq V_{CC}$ – 0.2 V, Address: V_{IH} or V_{IL}, $\overline{WE}$, $\overline{OE}$: V_{IH}, I_O = 0 mA	$t_{RAS} \leq$ 1 μs		600	μA	1, 2
$\overline{CAS}$ before $\overline{RAS}$ self refresh current (only for the μPD42S65805)		I_{CC7}	$\overline{RAS}$, $\overline{CAS}$: t_{RASS} = 5 ms, V_{CC} – 0.2 V ≤ $V_{IH} \leq V_{IH\ (MAX.)}$, 0 V ≤ V_{IL} ≤ 0.2 V, I_O = 0 mA			400	μA	2
Input leakage current		$I_{I\ (L)}$	V_I = 0 to 3.6 V, All other pins not under test = 0 V		–5	+5	μA	
Output leakage current		$I_{O\ (L)}$	V_O = 0 to 3.6 V, Output is disabled (Hi-Z)		–5	+5	μA	
High level output voltage		V_{OH}	I_O = –2.0 mA		2.4		V	
Low level output voltage		V_{OL}	I_O = +2.0 mA			0.4	V	

Notes 1. I_{CC1}, I_{CC3}, I_{CC4}, I_{CC5} and I_{CC6} depend on cycle rates (t_{RC} and t_{HPC}).

2. Specified values are obtained with outputs unloaded.

3. I_{CC1} and I_{CC3} are measured assuming that address can be changed once or less during $\overline{RAS} \leq V_{IL\ (MAX.)}$ and $\overline{CAS} \geq V_{IH\ (MIN.)}$.

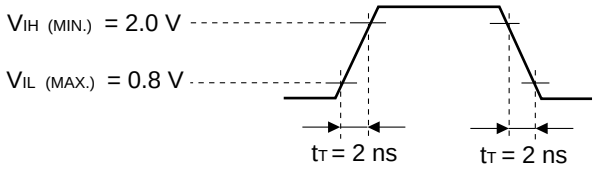
4. I_{CC3} is measured assuming that all column address inputs are held at either high or low.

5. I_{CC4} is measured assuming that all column address inputs are switched only once during each hyper page (EDO) cycle.

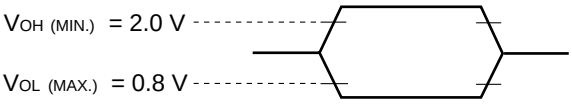
AC Characteristics (Recommended Operating Conditions unless otherwise noted)

AC Characteristics Test Conditions

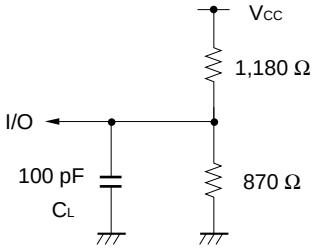
(1) Input timing specification



(2) Output timing specification



(3) Output load condition



Common to Read, Write, Read Modify Write Cycle

Parameter		Symbol	t_{RAC} = 50 ns		t_{RAC} = 60 ns		Unit	Notes
			MIN.	MAX.	MIN.	MAX.		
Read / Write cycle time		t_{RC}	84	–	104	–	ns	
$\overline{RAS}$ precharge time		t_{RP}	30	–	40	–	ns	
$\overline{CAS}$ precharge time		t_{CPN}	7	–	10	–	ns	
$\overline{RAS}$ pulse width		t_{RAS}	50	10,000	60	10,000	ns	1
$\overline{CAS}$ pulse width		t_{CAS}	8	10,000	10	10,000	ns	
$\overline{RAS}$ hold time		t_{RSH}	13	–	15	–	ns	
$\overline{CAS}$ hold time		t_{CSH}	38	–	40	–	ns	
$\overline{RAS}$ to $\overline{CAS}$ delay time		t_{RCD}	11	37	14	45	ns	2
$\overline{RAS}$ to column address delay time		t_{RAD}	9	25	12	30	ns	2
$\overline{CAS}$ to $\overline{RAS}$ precharge time		t_{CRP}	5	–	5	–	ns	3
Row address setup time		t_{ASR}	0	–	0	–	ns	
Row address hold time		t_{RAH}	7	–	10	–	ns	
Column address setup time		t_{ASC}	0	–	0	–	ns	
Column address hold time		t_{CAH}	7	–	10	–	ns	
$\overline{OE}$ lead time referenced to $\overline{RAS}$		t_{OES}	0	–	0	–	ns	
$\overline{CAS}$ to data setup time		t_{CLZ}	0	–	0	–	ns	
$\overline{OE}$ to data setup time		t_{OLZ}	0	–	0	–	ns	
$\overline{OE}$ to data delay time		t_{OED}	10	–	13	–	ns	
Transition time (rise and fall)		t_T	1	50	1	50	ns	
★ Refresh time	μPD42S65805	t_{REF}	–	128	–	128	ms	4
	μPD4264805, 4265805		–	64	–	64	ms	

Notes 1. In $\overline{CAS}$ before $\overline{RAS}$ refresh cycles, $t_{RAS(MAX)}$ is 100 μs.
If 10 μs < t_{RAS} < 100 μs, $\overline{RAS}$ precharge time for $\overline{CAS}$ before $\overline{RAS}$ self refresh (t_{RPS}) is applied.

2. For read cycles, access time is defined as follows:

Input conditions	Access time	Access time from $\overline{RAS}$
$t_{RAD} \leq t_{RAD\ (MAX.)}$ and $t_{RCD} \leq t_{RCD\ (MAX.)}$	$t_{RAC\ (MAX.)}$	$t_{RAC\ (MAX.)}$
$t_{RAD} > t_{RAD\ (MAX.)}$ and $t_{RCD} \leq t_{RCD\ (MAX.)}$	$t_{AA\ (MAX.)}$	$t_{RAD} + t_{AA\ (MAX.)}$
$t_{RCD} > t_{RCD\ (MAX.)}$	$t_{CAC\ (MAX.)}$	$t_{RCD} + t_{CAC\ (MAX.)}$

$t_{RAD\ (MAX.)}$ and $t_{RCD\ (MAX.)}$ are specified as reference points only ; they are not restrictive operating parameters. They are used to determine which access time (t_{RAC}, t_{AA} or t_{CAC}) is to be used for finding out when output data will be available. Therefore, the input conditions $t_{RAD} \geq t_{RAD\ (MAX.)}$ and $t_{RCD} \geq t_{RCD\ (MAX.)}$ will not cause any operation problems.

3. $t_{CRP\ (MIN.)}$ requirement is applied to $\overline{RAS}$, $\overline{CAS}$ cycles.

4. This specification is applied only to the μPD42S65805.

Read Cycle

Parameter	Symbol	t_{RAC} = 50 ns		t_{RAC} = 60 ns		Unit	Notes
		MIN.	MAX.	MIN.	MAX.		
Access time from $\overline{RAS}$	t_{RAC}	–	50	–	60	ns	1
Access time from $\overline{CAS}$	t_{CAC}	–	13	–	15	ns	1
Access time from column address	t_{AA}	–	25	–	30	ns	1
Access time from $\overline{OE}$	t_{OEA}	–	13	–	15	ns	
Column address lead time referenced to $\overline{RAS}$	t_{RAL}	25	–	30	–	ns	
Read command setup time	t_{RCS}	0	–	0	–	ns	
Read command hold time referenced to $\overline{RAS}$	t_{RRH}	0	–	0	–	ns	2
Read command hold time referenced to $\overline{CAS}$	t_{RCH}	0	–	0	–	ns	2
Output buffer turn-off delay time from $\overline{OE}$	t_{OEZ}	0	10	0	13	ns	3
$\overline{CAS}$ hold time to $\overline{OE}$	t_{CHO}	5	–	5	–	ns	4

Notes 1. For read cycles, access time is defined as follows:

Input conditions	Access time	Access time from $\overline{RAS}$
$t_{RAD} \leq t_{RAD\ (MAX.)}$ and $t_{RCD} \leq t_{RCD\ (MAX.)}$	$t_{RAC\ (MAX.)}$	$t_{RAC\ (MAX.)}$
$t_{RAD} > t_{RAD\ (MAX.)}$ and $t_{RCD} \leq t_{RCD\ (MAX.)}$	$t_{AA\ (MAX.)}$	$t_{RAD} + t_{AA\ (MAX.)}$
$t_{RCD} > t_{RCD\ (MAX.)}$	$t_{CAC\ (MAX.)}$	$t_{RCD} + t_{CAC\ (MAX.)}$

$t_{RAD\ (MAX.)}$ and $t_{RCD\ (MAX.)}$ are specified as reference points only; they are not restrictive operating parameters. They are used to determine which access time (t_{RAC}, t_{AA} or t_{CAC}) is to be used for finding out when output data will be available. Therefore, the input conditions $t_{RAD} \geq t_{RAD\ (MAX.)}$ and $t_{RCD} \geq t_{RCD\ (MAX.)}$ will not cause any operation problems.

2. Either $t_{RCH\ (MIN.)}$ or $t_{RRH\ (MIN.)}$ should be met in read cycles.

3. $t_{OEZ(MAX.)}$ defines the time when the output achieves the condition of Hi-Z and is not referenced to V_{OH} or V_{OL}.

4. $\overline{WE}$: inactive (in read cycle)
$\overline{CAS}$: inactive, $\overline{OE}$: active ····· t_{CHO} is effective.
$\overline{CAS}$, $\overline{OE}$: active ····· t_{OCH} is effective.

Write Cycle

Parameter	Symbol	t_{RAC} = 50 ns		t_{RAC} = 60 ns		Unit	Notes
		MIN.	MAX.	MIN.	MAX.		
$\overline{WE}$ hold time referenced to $\overline{CAS}$	t_{WCH}	7	–	10	–	ns	1
$\overline{WE}$ pulse width	t_{WP}	7	–	10	–	ns	1
$\overline{WE}$ lead time referenced to $\overline{RAS}$	t_{RWL}	13	–	15	–	ns	
$\overline{WE}$ lead time referenced to $\overline{CAS}$	t_{CWL}	7	–	10	–	ns	
$\overline{WE}$ setup time	t_{WCS}	0	–	0	–	ns	2
$\overline{OE}$ hold time	t_{OEH}	0	–	0	–	ns	
Data-in setup time	t_{DS}	0	–	0	–	ns	3
Data-in hold time	t_{DH}	7	–	10	–	ns	3

Notes 1. $t_{WP\ (MIN.)}$ is applied to late write cycles or read modify write cycles. In early write cycles, $t_{WCH\ (MIN.)}$ should be met.

2. If $t_{WCS} \geq t_{WCS\ (MIN.)}$, the cycle is an early write cycle and the data out will remain Hi-Z through the entire cycle.

3. $t_{DS\ (MIN.)}$ and $t_{DH\ (MIN.)}$ are referenced to the $\overline{CAS}$ falling edge in early write cycles. In late write cycles and read modify write cycles, they are referenced to the $\overline{WE}$ falling edge.

Read Modify Write Cycle

Parameter	Symbol	t_{RAC} = 50 ns		t_{RAC} = 60 ns		Unit	Note
		MIN.	MAX.	MIN.	MAX.		
Read modify write cycle time	t_{RWC}	107	–	133	–	ns	
$\overline{RAS}$ to $\overline{WE}$ delay time	t_{RWD}	64	–	77	–	ns	1
$\overline{CAS}$ to $\overline{WE}$ delay time	t_{CWD}	27	–	32	–	ns	1
Column address to $\overline{WE}$ delay time	t_{AWD}	39	–	47	–	ns	1

Note 1. If $t_{WCS} \geq t_{WCS\ (MIN.)}$, the cycle is an early write cycle and the data out will remain Hi-Z through the entire cycle. If $t_{RWD} \geq t_{RWD\ (MIN.)}$, $t_{CWD} \geq t_{CWD\ (MIN.)}$, $t_{AWD} \geq t_{AWD\ (MIN.)}$ and $t_{CPWD} \geq t_{CPWD\ (MIN.)}$, the cycle is a read modify write cycle and the data out will contain data read from the selected cell. If neither of the above conditions is met, the state of the data out is indeterminate.

Hyper Page Mode (EDO)

Parameter	Symbol	t_{RAC} = 50 ns		t_{RAC} = 60 ns		Unit	Notes
		MIN.	MAX.	MIN.	MAX.		
Read / Write cycle time	t_{HPC}	20	–	25	–	ns	1
$\overline{RAS}$ pulse width	t_{RASP}	50	125,000	60	125,000	ns	
$\overline{CAS}$ pulse width	t_{HCAS}	8	10,000	10	10,000	ns	
$\overline{CAS}$ precharge time	t_{CP}	7	–	10	–	ns	
Access time from $\overline{CAS}$ precharge	t_{ACP}	–	30	–	35	ns	
$\overline{CAS}$ precharge to $\overline{WE}$ delay time	t_{CPWD}	41	–	52	–	ns	2
$\overline{RAS}$ hold time from $\overline{CAS}$ precharge	t_{RHCP}	30	–	35	–	ns	
Read modify write cycle time	t_{HPRWC}	52	–	66	–	ns	
Data output hold time	t_{DHC}	5	–	5	–	ns	
$\overline{OE}$ to $\overline{CAS}$ hold time	t_{OCH}	5	–	5	–	ns	3
$\overline{OE}$ precharge time	t_{OEP}	5	–	5	–	ns	
Output buffer turn-off delay from $\overline{WE}$	t_{WEZ}	0	10	0	13	ns	4, 5
$\overline{WE}$ pulse width	t_{WPZ}	7	–	10	–	ns	5
Output buffer turn-off delay from $\overline{RAS}$	t_{OFR}	0	10	0	13	ns	4, 5
Output buffer turn-off delay from $\overline{CAS}$	t_{OFC}	0	10	0	13	ns	4, 5

Notes 1. $t_{HPC\ (MIN.)}$ is applied to $\overline{CAS}$ access.

2. If $t_{WCS} \geq t_{WCS\ (MIN.)}$, the cycle is an early write cycle and the data out will remain Hi-Z through the entire cycle. If $t_{RWD} \geq t_{RWD\ (MIN.)}$, $t_{CWD} \geq t_{CWD\ (MIN.)}$, $t_{AWD} \geq t_{AWD\ (MIN.)}$ and $t_{CPWD} \geq t_{CPWD\ (MIN.)}$, the cycle is a read modify write cycle and the data out will contain data read from the selected cell. If neither of the above conditions is met, the state of the data out is indeterminate.

3. $\overline{WE}$: inactive (in read cycle)
$\overline{CAS}$: inactive, $\overline{OE}$: active ····· t_{CHO} is effective.
$\overline{CAS}$, $\overline{OE}$: active ····· t_{OCH} is effective.

4. $t_{OFC\ (MAX.)}$, $t_{OFR\ (MAX.)}$ and $t_{WEZ\ (MAX.)}$ define the time when the output achieves the conditions of Hi-Z and is not referenced to V_{OH} or V_{OL}.

5. To make I/Os to Hi-Z in read cycle, it is necessary to control $\overline{RAS}$, $\overline{CAS}$, $\overline{WE}$, $\overline{OE}$ as follows. The effective specification depends on state of each signal.

(1) Both $\overline{RAS}$ and $\overline{CAS}$ are inactive (at the end of the read cycle)
$\overline{WE}$: inactive, $\overline{OE}$: active
t_{OFC} is effective when $\overline{RAS}$ is inactivated before $\overline{CAS}$ is inactivated.
t_{OFR} is effective when $\overline{CAS}$ is inactivated before $\overline{RAS}$ is inactivated.
The slower of t_{OFC} and t_{OFR} becomes effective.

(2) Both $\overline{RAS}$ and $\overline{CAS}$ are active or either $\overline{RAS}$ or $\overline{CAS}$ is active (in read cycle)
$\overline{WE}$, $\overline{OE}$: inactive ····· t_{OEZ} is effective.
Both $\overline{RAS}$ and $\overline{CAS}$ are inactive or $\overline{RAS}$ is active and $\overline{CAS}$ is inactive (at the end of read cycle)
$\overline{WE}$, $\overline{OE}$: active and either t_{RRH} or t_{RCH} must be met ····· t_{WEZ} and t_{WPZ} are effective.
The faster of t_{OEZ} and t_{WEZ} becomes effective.

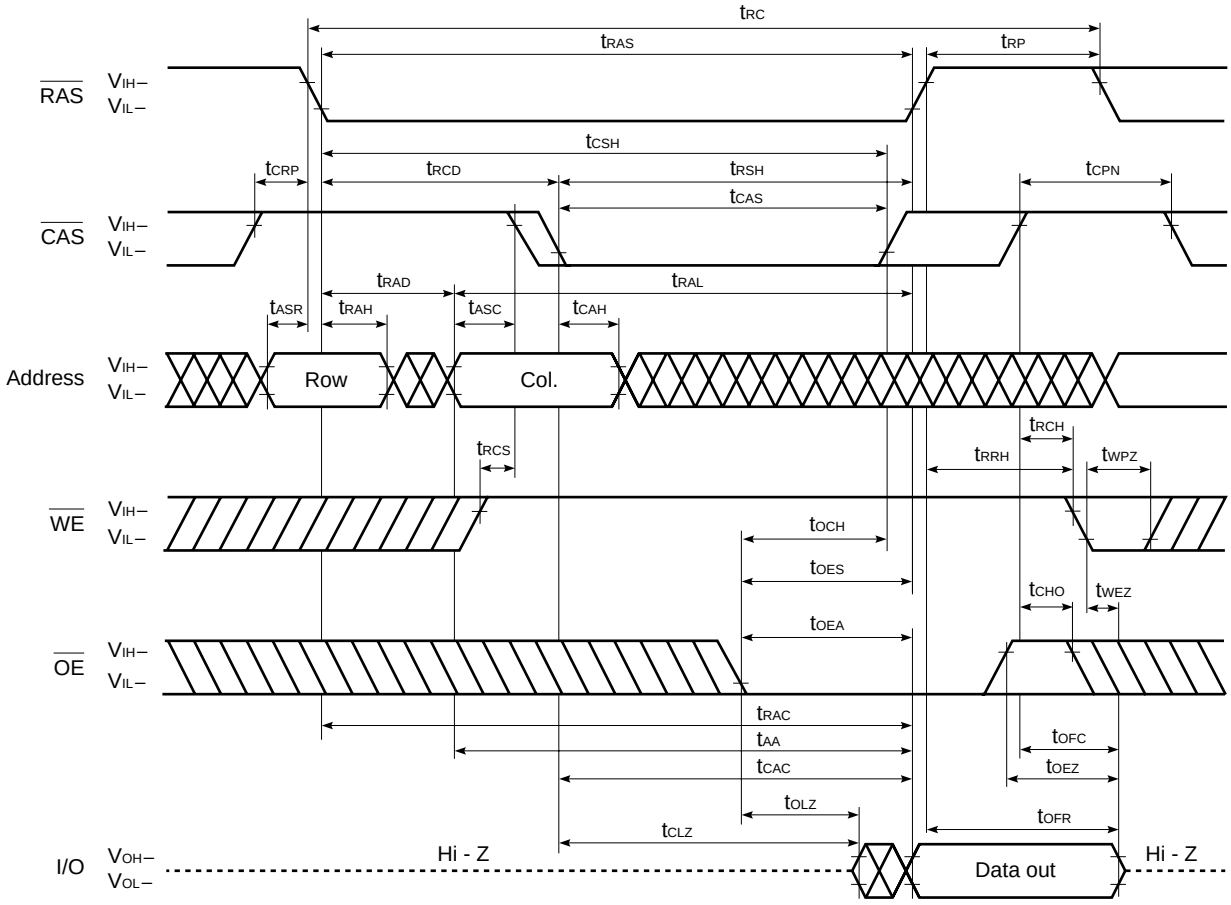
The faster of (1) and (2) becomes effective.

Refresh Cycle

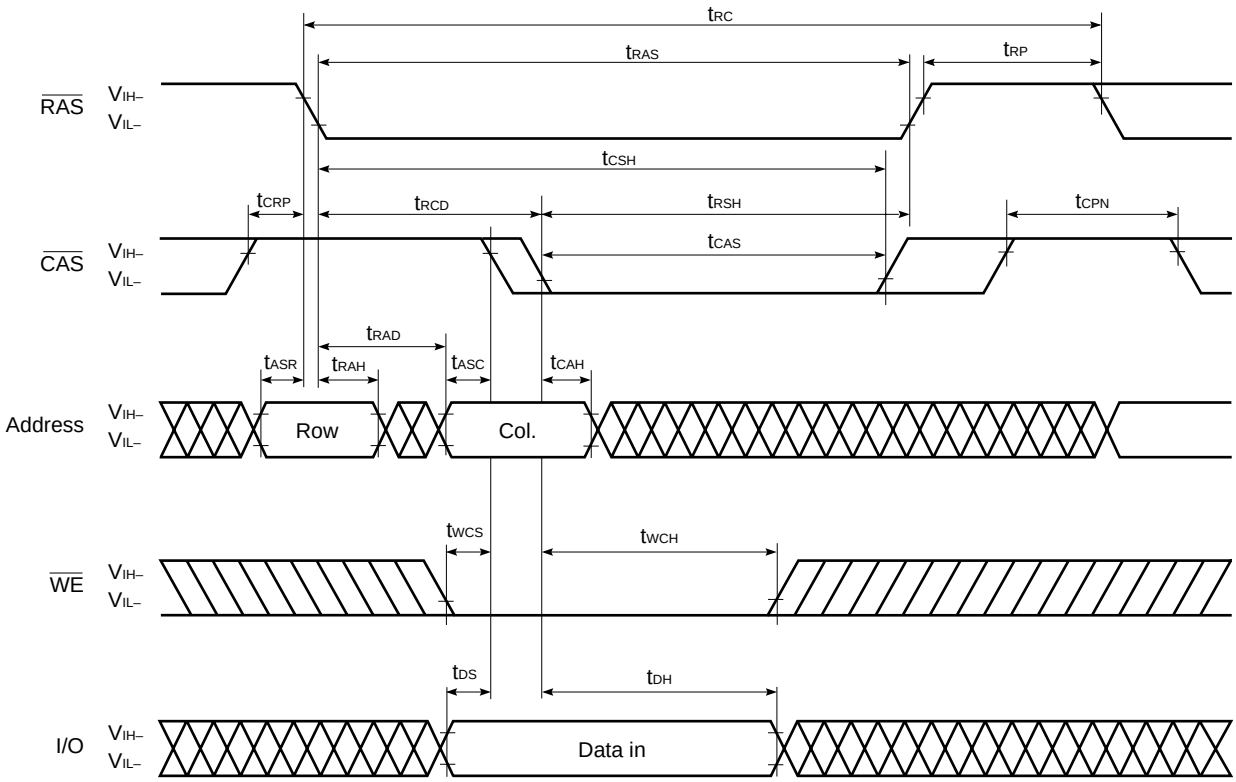
Parameter	Symbol	t_{RAC} = 50 ns		t_{RAC} = 60 ns		Unit	Note
		MIN.	MAX.	MIN.	MAX.		
$\overline{CAS}$ setup time	t_{CSR}	5	–	5	–	ns	
$\overline{CAS}$ hold time ($\overline{CAS}$ before $\overline{RAS}$ refresh)	t_{CHR}	10	–	10	–	ns	
$\overline{RAS}$ precharge $\overline{CAS}$ hold time	t_{RPC}	5	–	5	–	ns	
$\overline{RAS}$ pulse width ($\overline{CAS}$ befoe $\overline{RAS}$ self refresh)	t_{RASS}	100	–	100	–	μs	1
$\overline{RAS}$ precharge time ($\overline{CAS}$ before $\overline{RAS}$ self refresh)	t_{RPS}	90	–	110	–	ns	1
$\overline{CAS}$ hold time ($\overline{CAS}$ before $\overline{RAS}$ self refresh)	t_{CHS}	–50	–	–50	–	ns	1
$\overline{WE}$ setup time	t_{WSR}	10	–	10	–	ns	
$\overline{WE}$ hold time	t_{WHR}	15	–	15	–	ns	

Note 1. This specification is applied only to the μPD42S65805.

Read Cycle

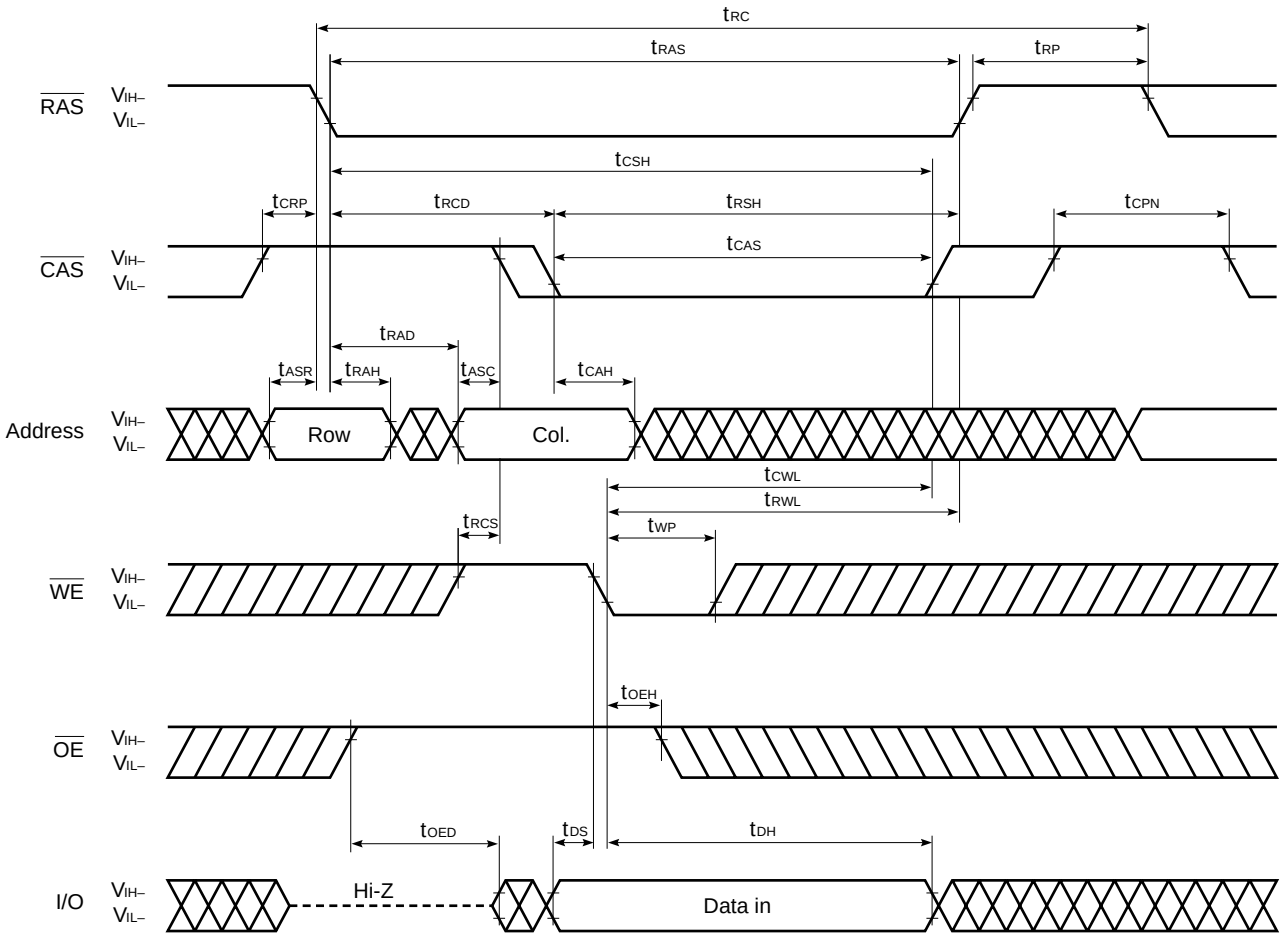

tRC
tRAS
tRP
RAS
VIH–
VIL–
tCSH
tCRP
tRCD
tRSH
tCPN
tCAS
CAS
tRAD
tRAL
tASR
tRAH
tASC
tCAH
Address
Row
Col.
tRCH
tRCS
tRRH
tWPZ
WE
tOCH
tOES
tCHO
tWEZ
tOEA
OE
tRAC
tAA
tOFC
tCAC
tOEZ
tOLZ
tOFR
tCLZ
I/O
VOH–
VOL–
Hi - Z
Data out
Hi - Z

Early Write Cycle

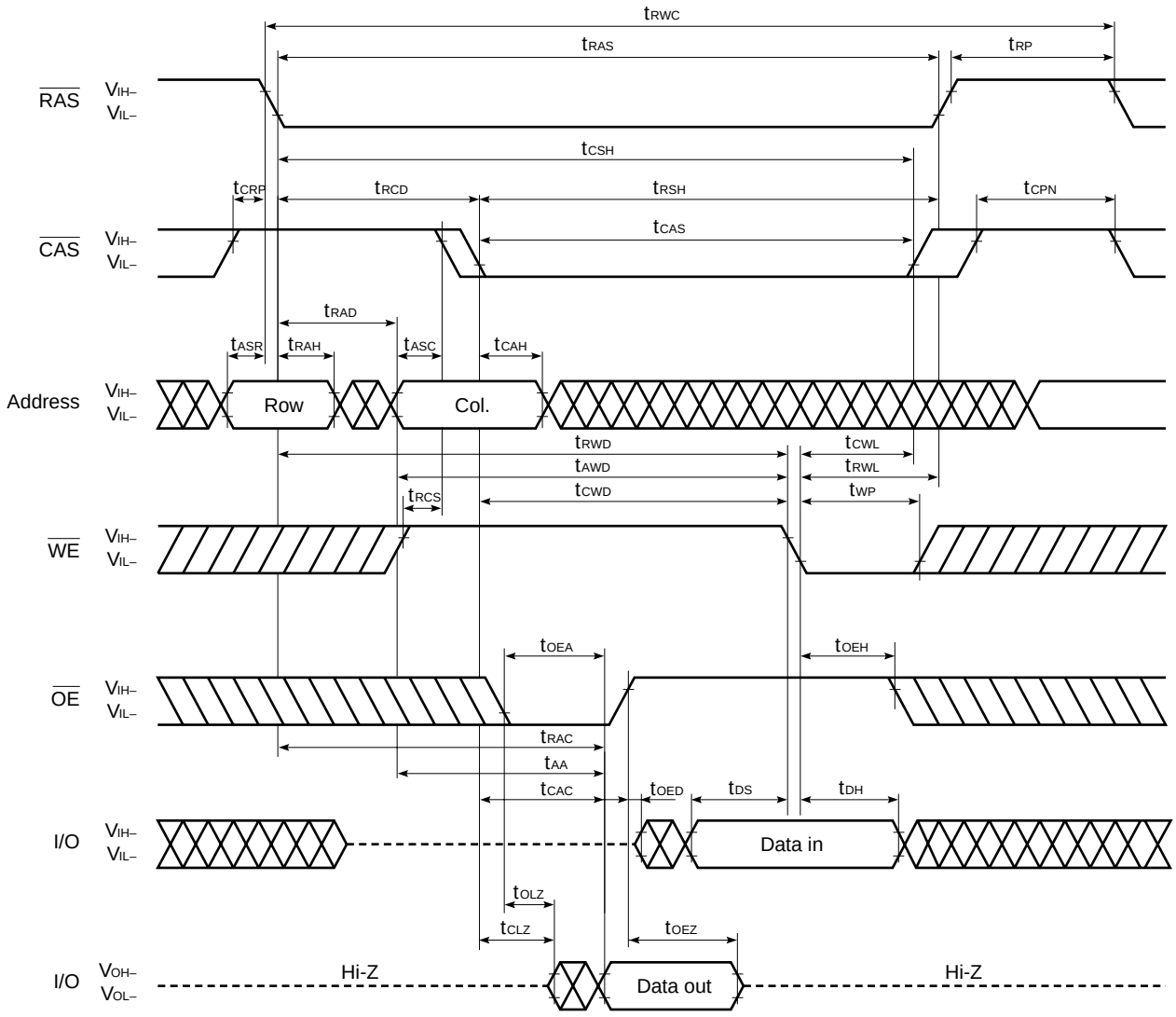


Remark $\overline{OE}$: Don't care

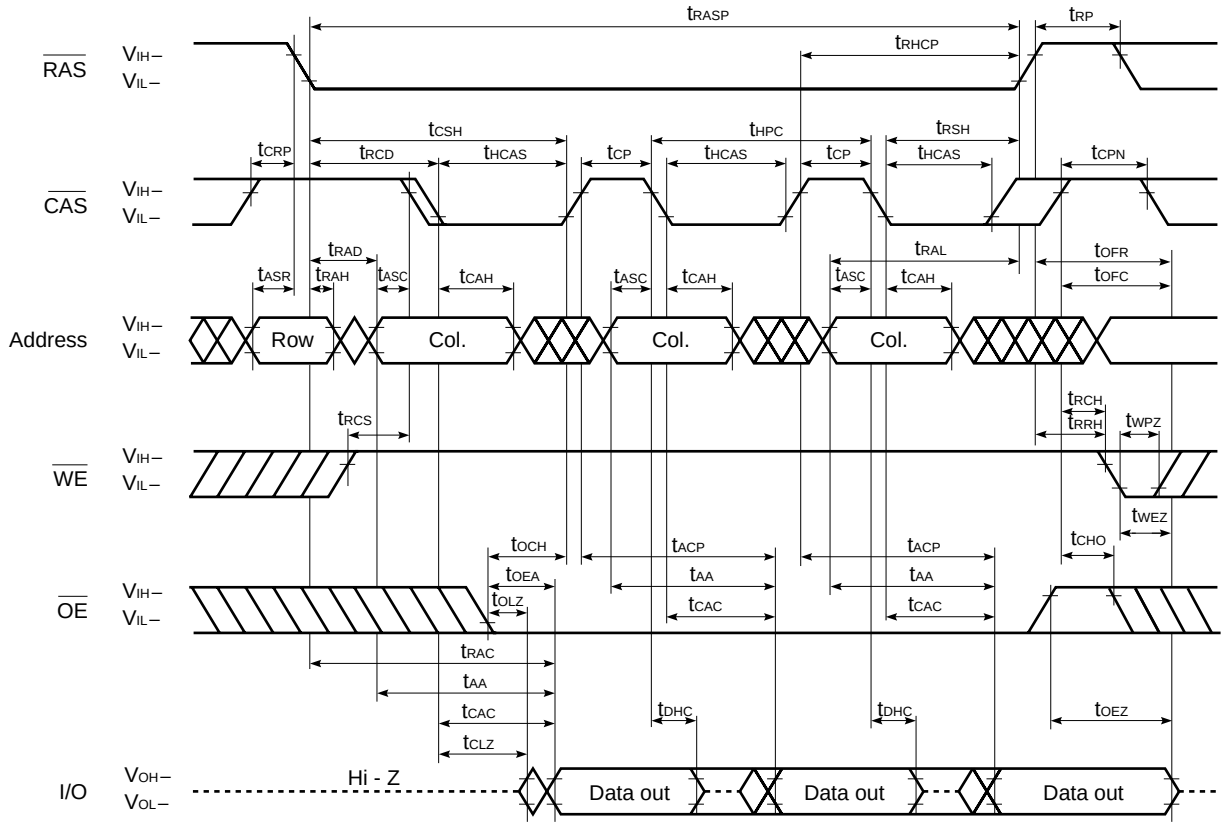
Late Write Cycle



Read Modify Write Cycle

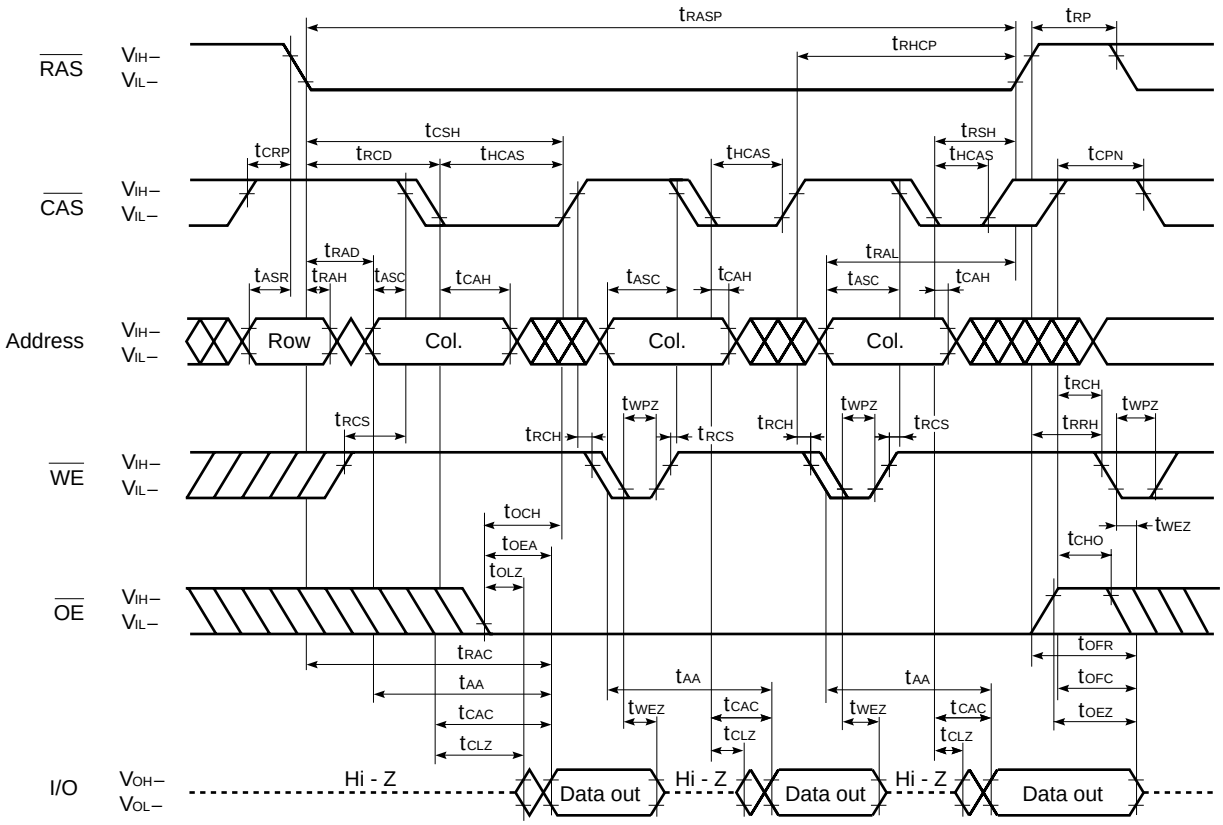


Hyper Page Mode (EDO) Read Cycle



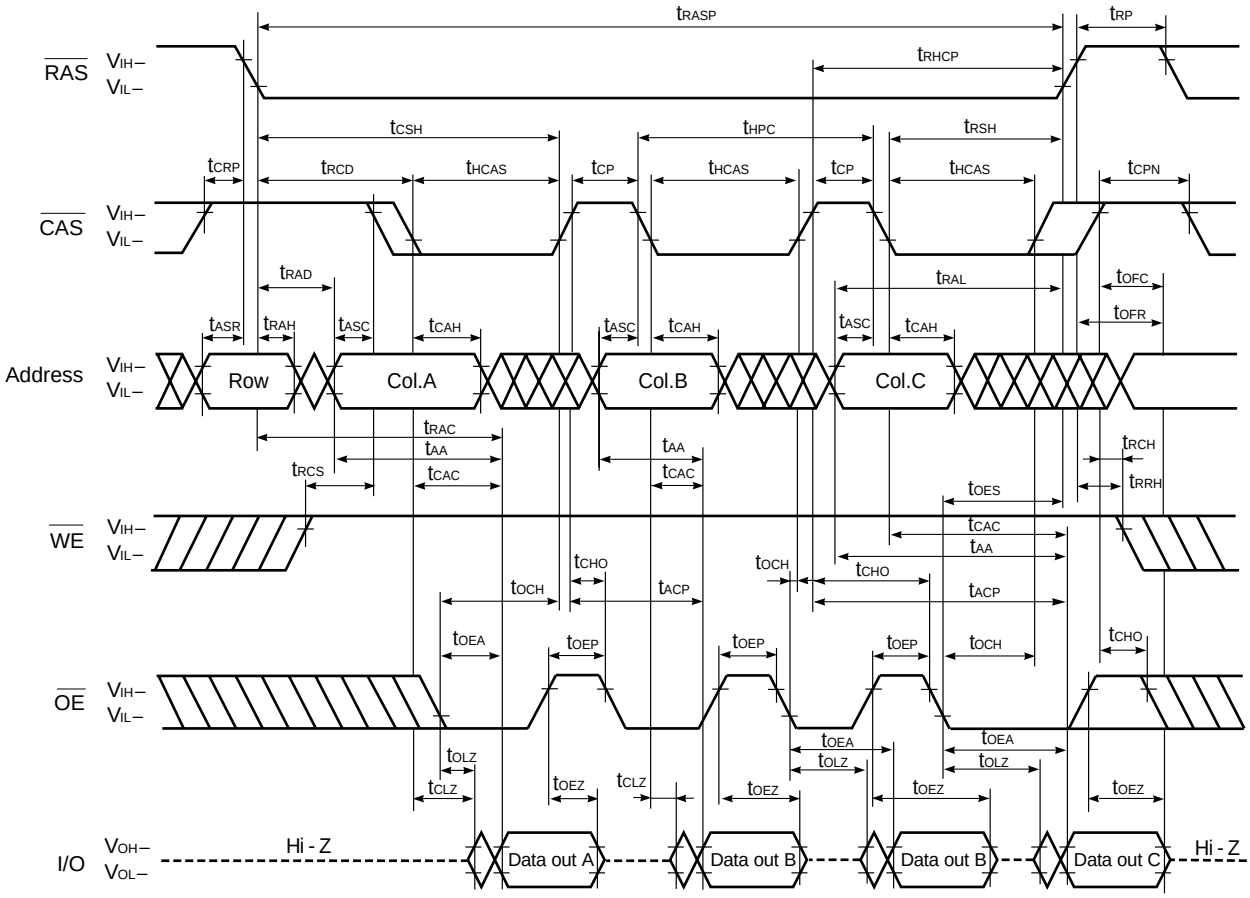
Remark In the hyper page mode (EDO), read, write and read modify write cycles are available for each of the consecutive $\overline{CAS}$ cycles within the same $\overline{RAS}$ cycle.

Hyper Page Mode (EDO) Read Cycle ($\overline{WE}$ Control)



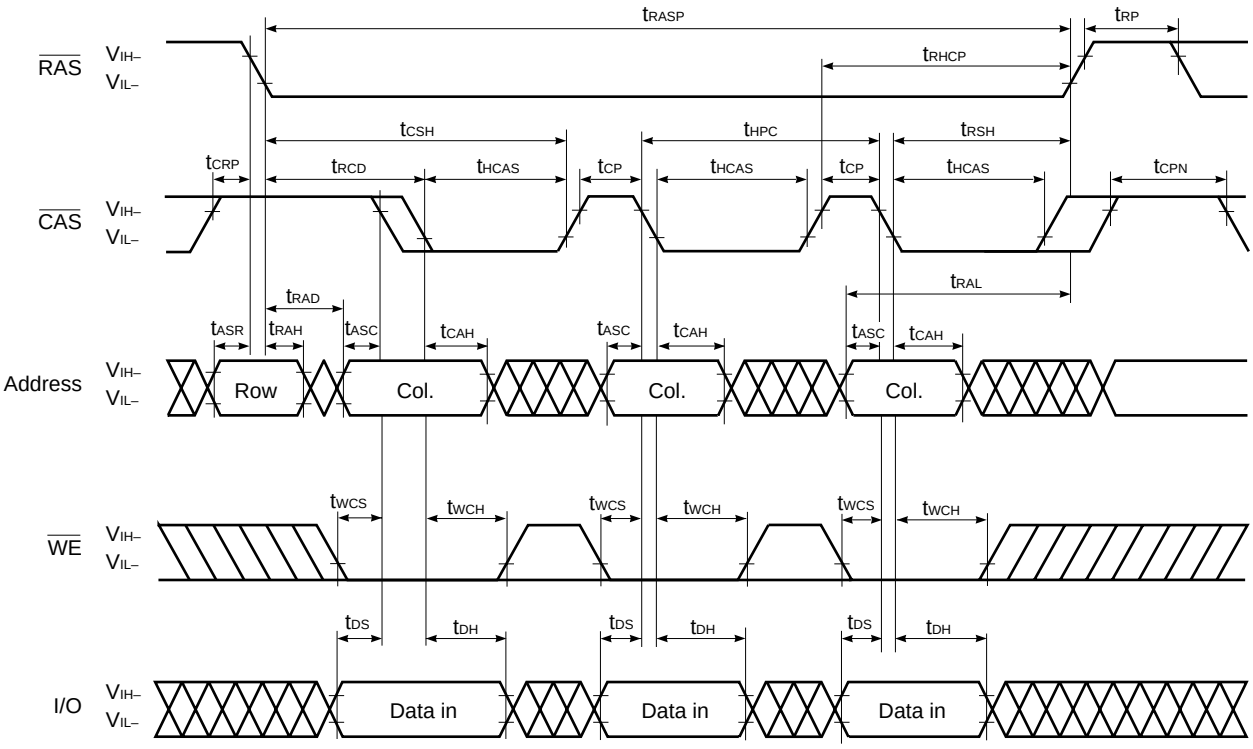
Remark In the hyper page mode (EDO), read, write and read modify write cycles are available for each of the consecutive $\overline{CAS}$ cycles within the same $\overline{RAS}$ cycle.

Hyper Page Mode (EDO) Read Cycle ($\overline{OE}$ Control)



Remark In the hyper page mode (EDO), read, write and read modify write cycles are available for each of the consecutive $\overline{CAS}$ cycles within the same $\overline{RAS}$ cycle.

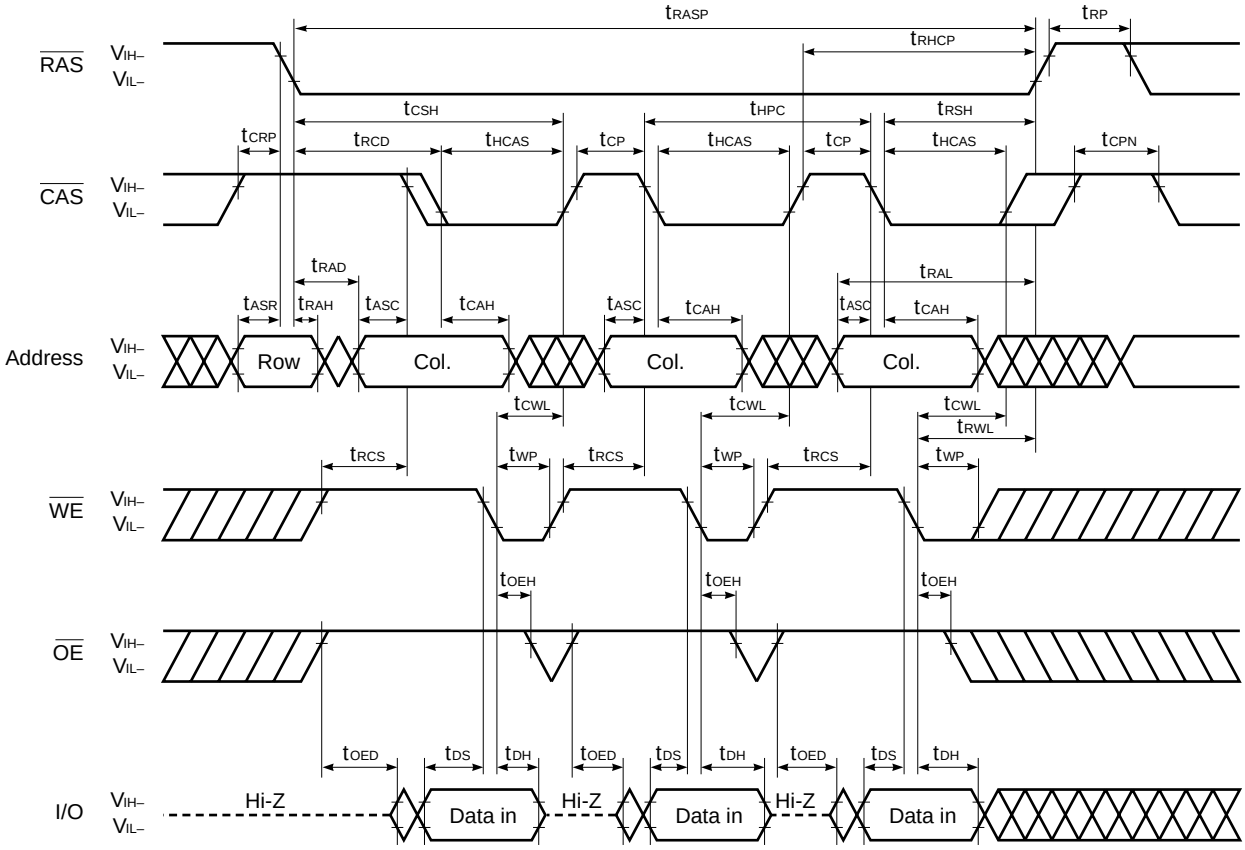
Hyper Page Mode (EDO) Early Write Cycle



Remarks 1. $\overline{OE}$: Don't care

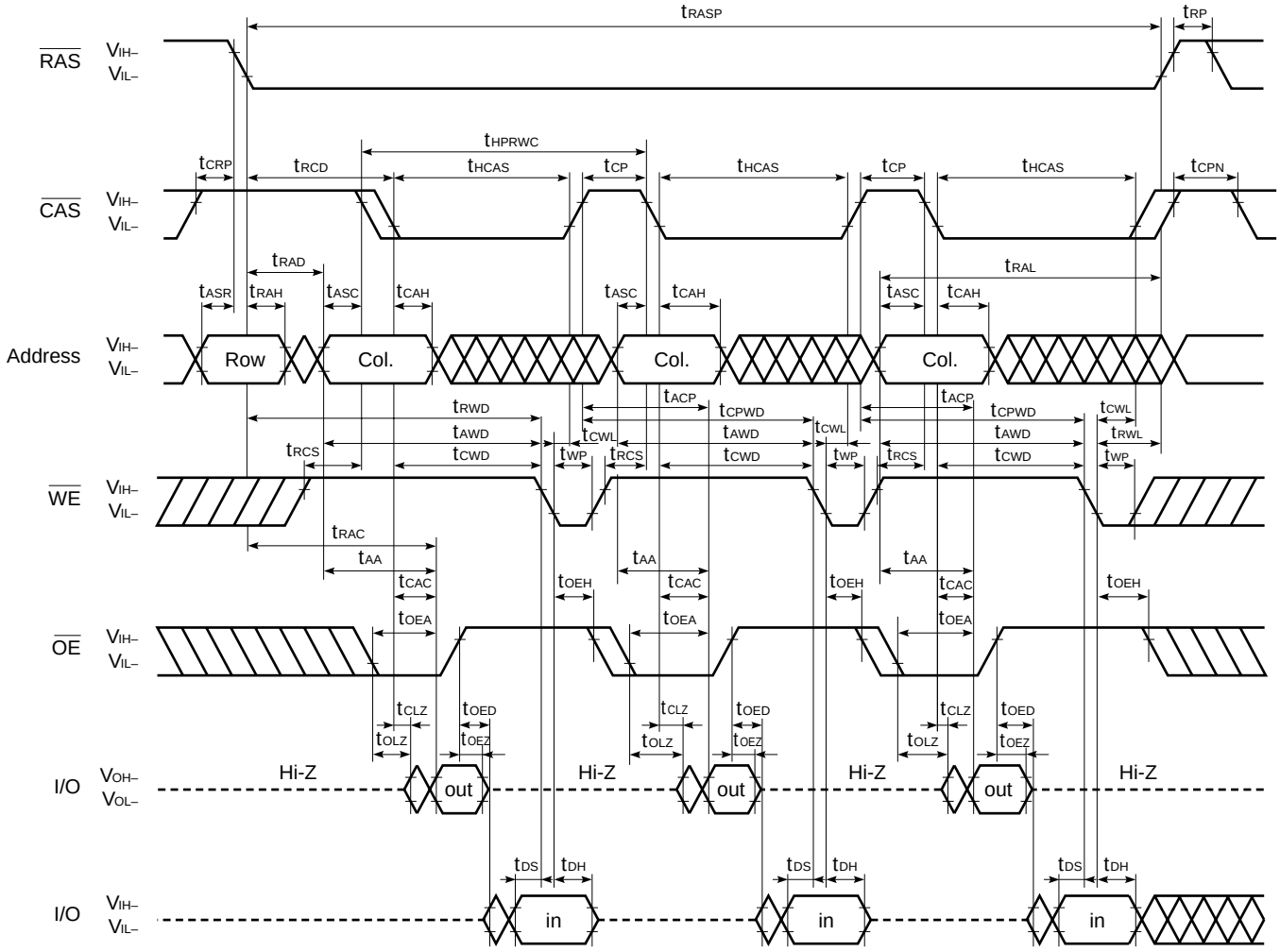
2. In the hyper page mode (EDO), read, write and read modify write cycles are available for each of the consecutive $\overline{CAS}$ cycles within the same $\overline{RAS}$ cycle.

Hyper Page Mode (EDO) Late Write Cycle



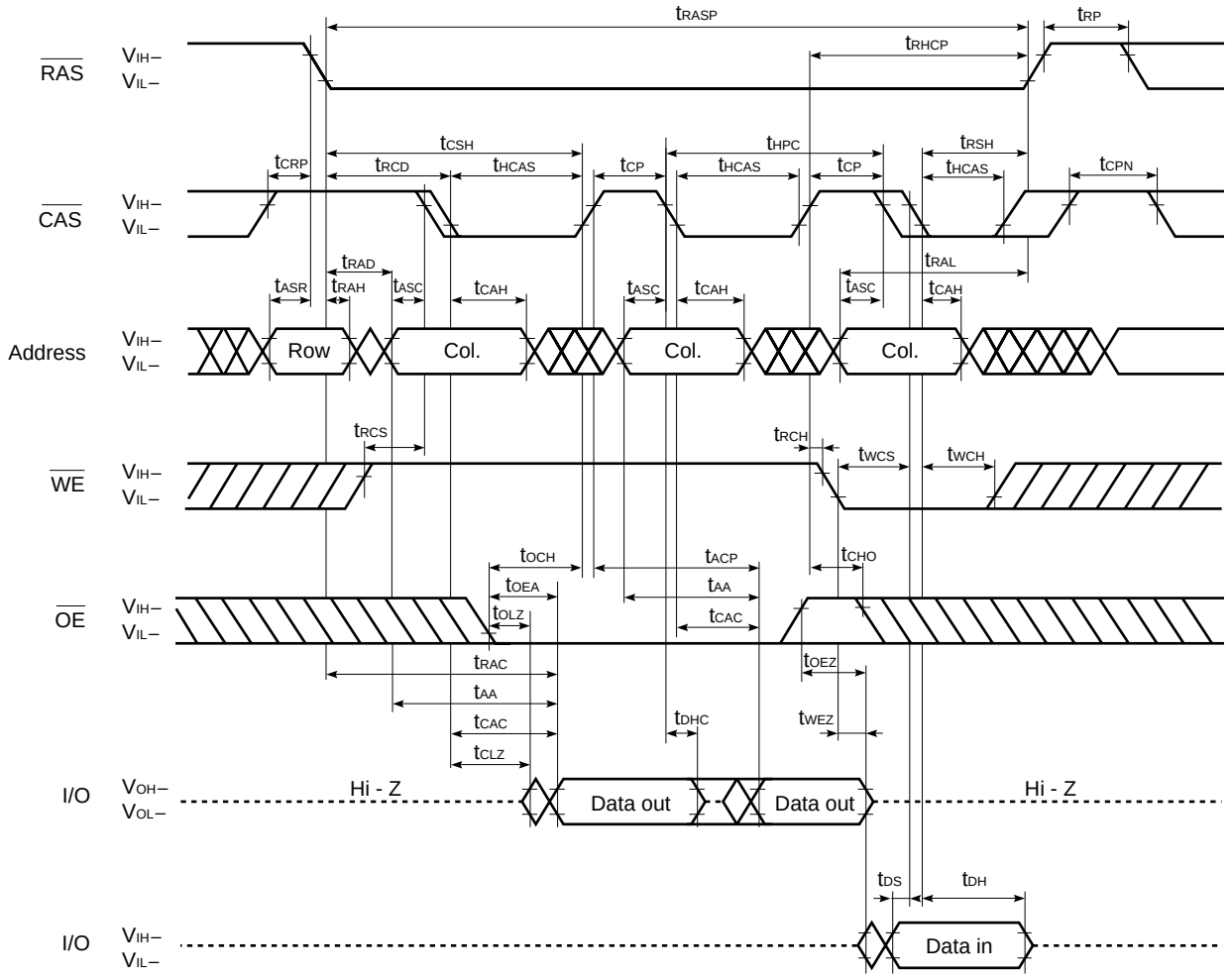
Remark In the hyper page mode (EDO), read, write and read modify write cycles are available for each of the consecutive $\overline{CAS}$ cycles within the same $\overline{RAS}$ cycle.

Hyper Page Mode (EDO) Read Modify Write Cycle



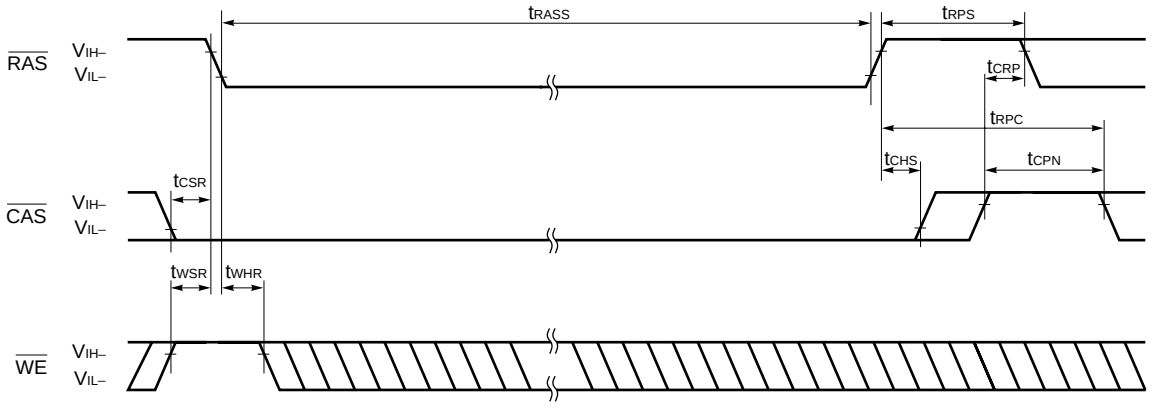
Remark In the hyper page mode (EDO), read, write and read modify write cycles are available for each of the consecutive $\overline{CAS}$ cycles within the same $\overline{RAS}$ cycle.

Hyper Page Mode (EDO) Read and Write Cycle



Remark In the hyper page mode (EDO), read, write and read modify write cycles are available for each of the consecutive $\overline{CAS}$ cycles within the same $\overline{RAS}$ cycle.

★ **$\overline{CAS}$ Before $\overline{RAS}$ Self Refresh Cycle (Only for the μPD42S65805)**



Remark Address, $\overline{OE}$: Don't care I/O: Hi-Z

Cautions on Use of $\overline{CAS}$ Before $\overline{RAS}$ Self Refresh

$\overline{CAS}$ before $\overline{RAS}$ self refresh can be used independently when used in combination with distributed $\overline{CAS}$ before $\overline{RAS}$ long refresh; However, when used in combination with burst $\overline{CAS}$ before $\overline{RAS}$ long refresh or with long $\overline{RAS}$ only refresh (both distributed and burst), the following cautions must be observed.

(1) Normal Combined Use of $\overline{CAS}$ Before $\overline{RAS}$ Self Refresh and Burst $\overline{CAS}$ Before $\overline{RAS}$ Long Refresh

When $\overline{CAS}$ before $\overline{RAS}$ self refresh and burst $\overline{CAS}$ before $\overline{RAS}$ long refresh are used in combination, please perform $\overline{CAS}$ before $\overline{RAS}$ refresh 4,096 times within a 64 ms interval just before and after setting $\overline{CAS}$ before $\overline{RAS}$ self refresh.

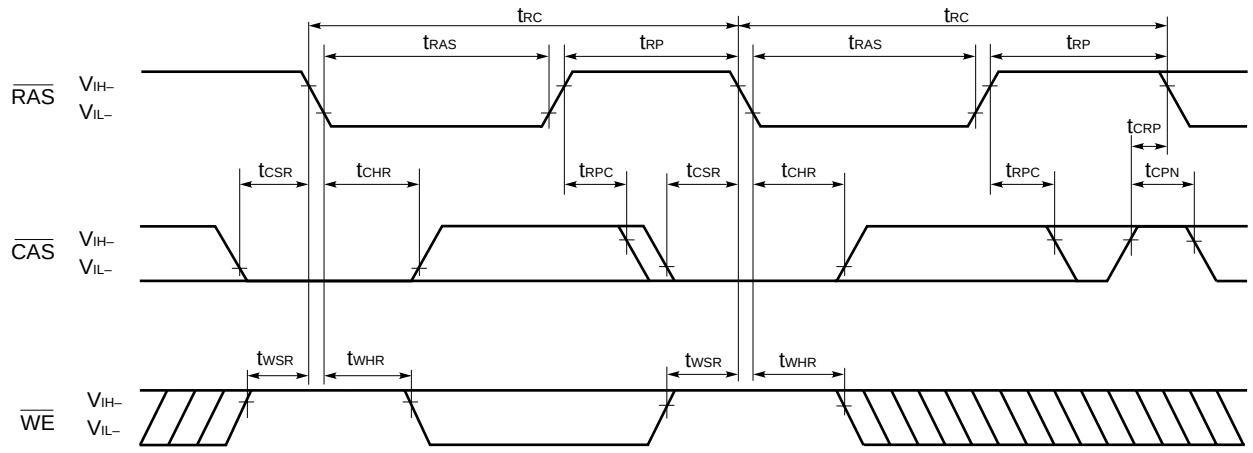
(2) Normal Combined Use of $\overline{CAS}$ Before $\overline{RAS}$ Self Refresh and Long $\overline{RAS}$ Only Refresh

When $\overline{CAS}$ before $\overline{RAS}$ self refresh and $\overline{RAS}$ only refresh are used in combination, please perform $\overline{RAS}$ only refresh 4,096 times within a 64 ms interval just before and after setting $\overline{CAS}$ before $\overline{RAS}$ self refresh.

(3) If $t_{RASS\ (MIN.)}$ is not satisfied at the beginning of $\overline{CAS}$ before $\overline{RAS}$ self refresh cycles (t_{RAS} < 100 μs), $\overline{CAS}$ before $\overline{RAS}$ refresh cycles will be executed one time.
If 10 μs < t_{RAS} < 100 μs, $\overline{RAS}$ precharge time for $\overline{CAS}$ before $\overline{RAS}$ self refresh (t_{RPS}) is applied.
And refresh cycles (4,096/128 ms) should be met.

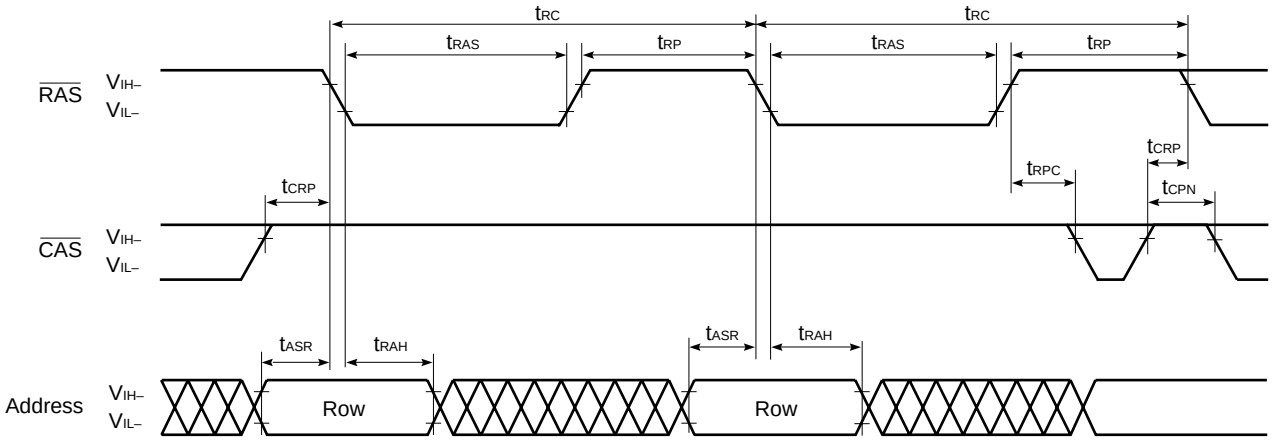
For details, please refer to **How to use DRAM** User's Manual.

$\overline{\text{CAS}}$ Before $\overline{\text{RAS}}$ Refresh Cycle



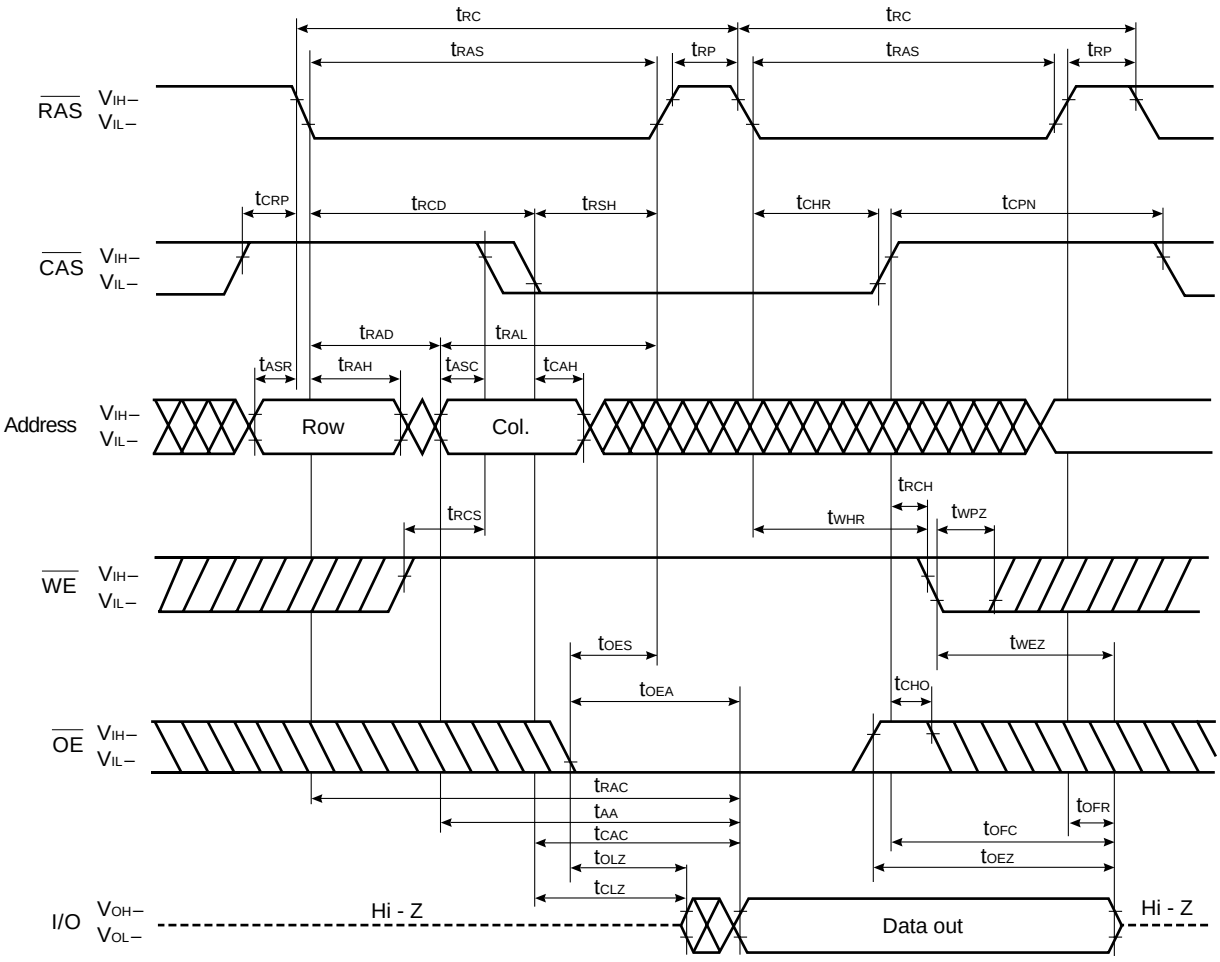
Remark Address, $\overline{\text{OE}}$: Don't care I/O: Hi-Z

$\overline{\text{RAS}}$ Only Refresh Cycle

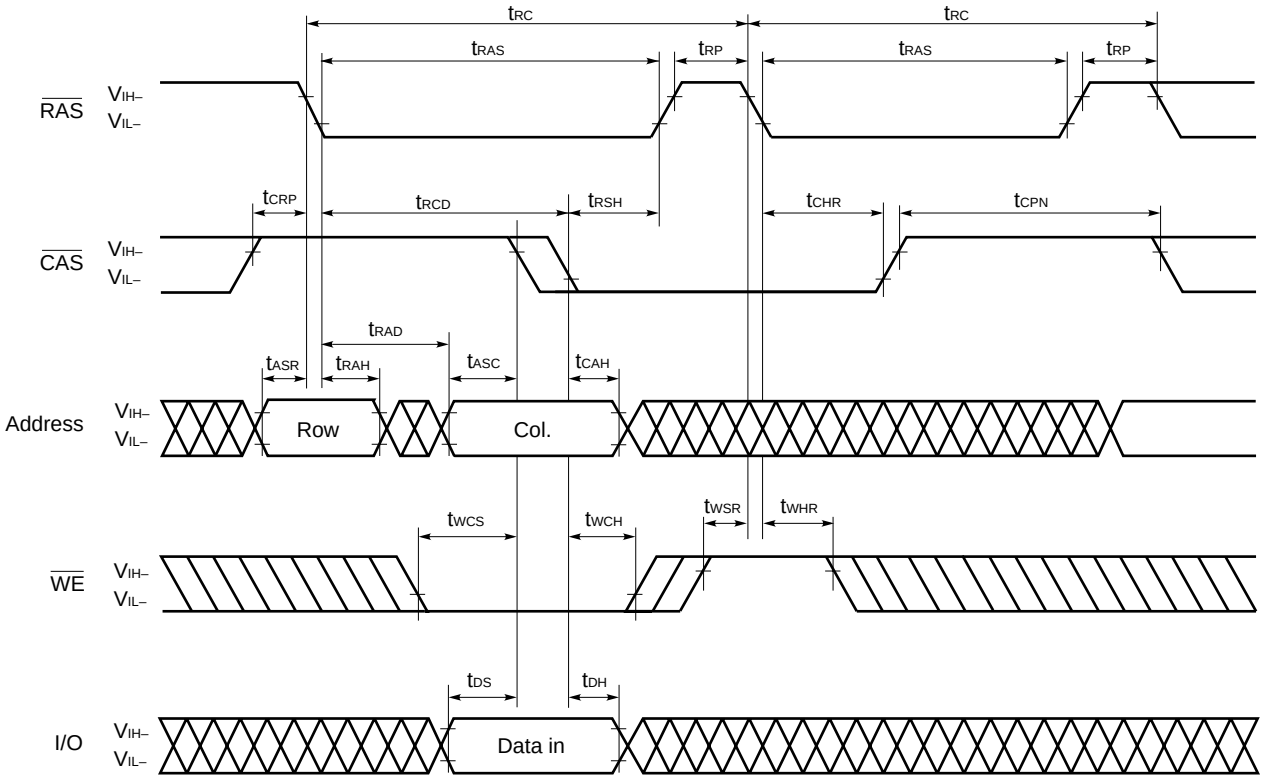


Remark $\overline{\text{WE}}$, $\overline{\text{OE}}$: Don't care I/O: Hi-Z

Hidden Refresh Cycle (Read)



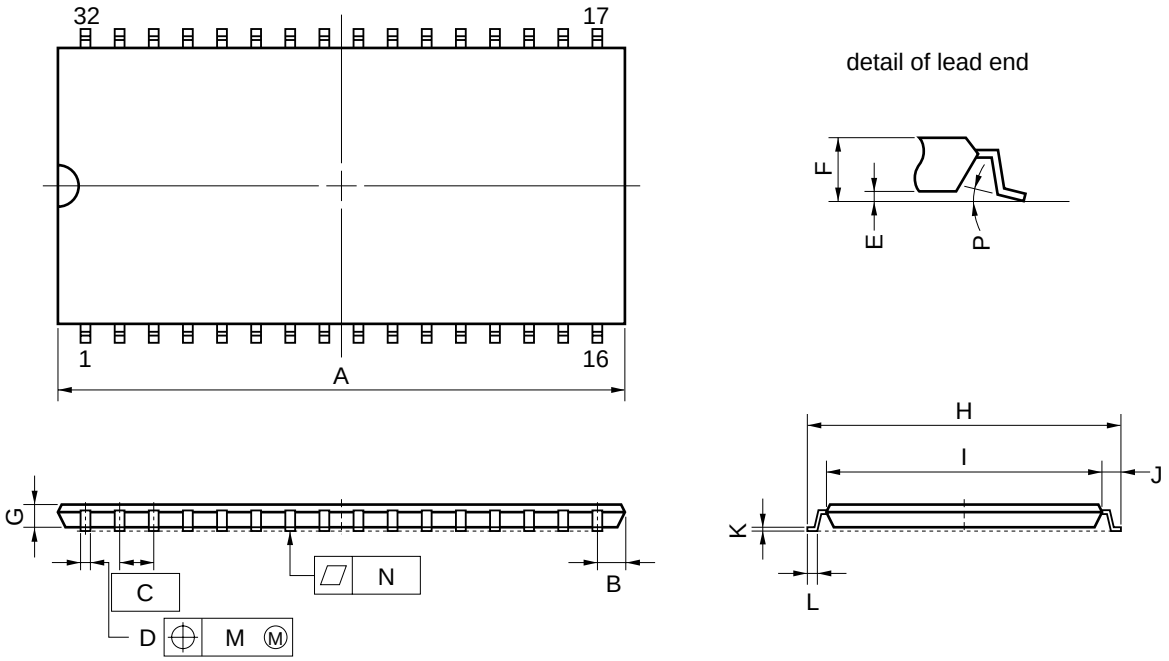
Hidden Refresh Cycle (Write)



Remark $\overline{OE}$: Don't care

Package Drawings

32PIN PLASTIC TSOP(II) (400 mil)



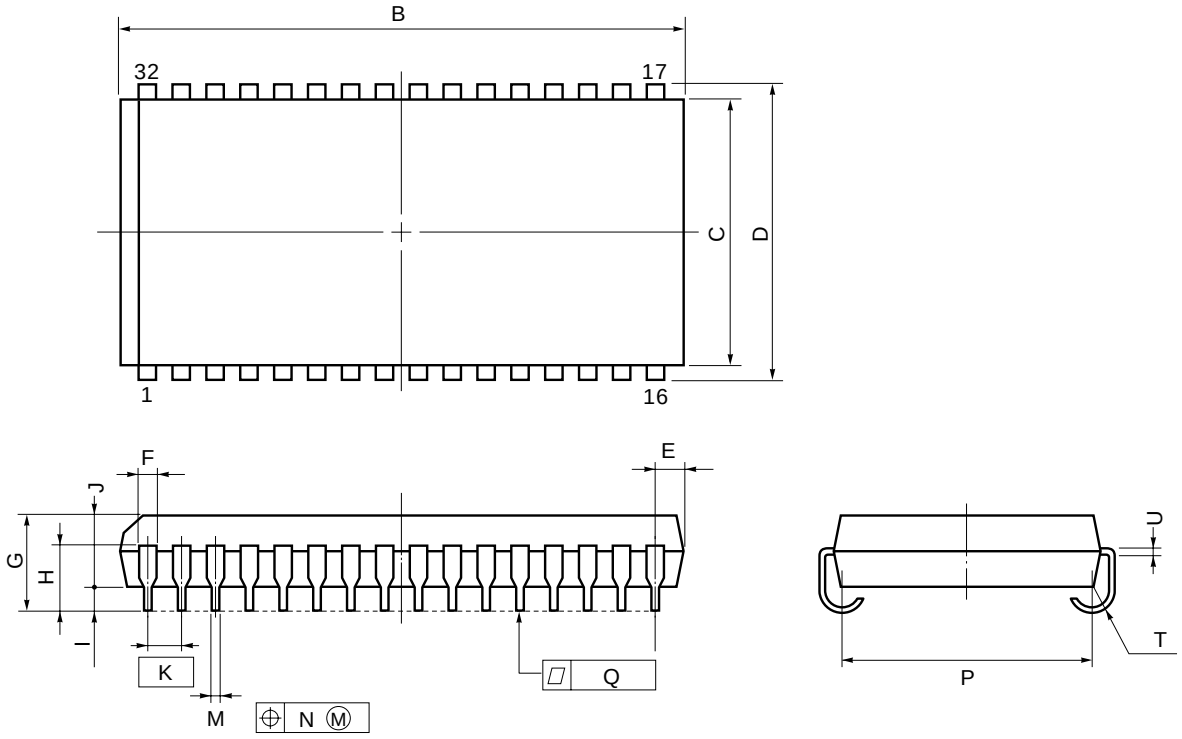
NOTE

Each lead centerline is located within 0.21 mm (0.009 inch) of its true position (T.P.) at maximum material condition.

ITEM	MILLIMETERS	INCHES
A	21.17 MAX.	0.834 MAX.
B	1.075 MAX.	0.043 MAX.
C	1.27 (T.P.)	0.050 (T.P.)
D	$0.42^{+0.08}_{-0.07}$	0.017±0.003
E	0.1±0.05	0.004±0.002
F	1.2 MAX.	0.048 MAX.
G	0.97	0.038
H	11.76±0.2	0.463±0.008
I	10.16±0.1	0.400±0.004
J	0.8±0.2	$0.031^{+0.009}_{-0.008}$
K	$0.145^{+0.025}_{-0.015}$	0.006±0.001
L	0.5±0.1	$0.020^{+0.004}_{-0.005}$
M	0.21	0.009
N	0.10	0.004
P	$3^{\circ}{}^{+7^{\circ}}_{-3^{\circ}}$	$3^{\circ}{}^{+7^{\circ}}_{-3^{\circ}}$

S32G5-50-7JD2

32 PIN PLASTIC SOJ (400 mil)



P32LE-400A

ITEM	MILLIMETERS	INCHES
B	21.06±0.2	0.829±0.008
C	10.16	0.400
D	11.18±0.2	0.440±0.008
E	1.005±0.1	$0.040^{+0.004}_{-0.005}$
F	0.74	0.029
G	3.5±0.2	0.138±0.008
H	2.545±0.2	0.100±0.008
I	0.8 MIN.	0.031 MIN.
J	2.6	0.102
K	1.27 (T.P.)	0.050 (T.P.)
M	0.40±0.10	$0.016^{+0.004}_{-0.005}$
N	0.12	0.005
P	9.4±0.20	0.370±0.008
Q	0.1	0.004
T	R 0.85	R 0.033
U	$0.20^{+0.10}_{-0.05}$	$0.008^{+0.004}_{-0.002}$

NOTE

Each lead centerline is located within 0.12 mm (0.005 inch) of its true position (T.P.) at maximum material condition.

★ Recommended Soldering Conditions

Please consult with our sales offices for soldering conditions of the μPD4264805, 42S65805, 4265805.

Types of Surface Mount Device

μPD4264805G5-7JD, 42S65805G5-7JD, 4265805G5-7JD: 32-pin plastic TSOP (II) (400 mil)
μPD4264805LE, 42S65805LE, 4265805LE: 32-pin plastic SOJ (400 mil)

[MEMO]

NOTES FOR CMOS DEVICES

① PRECAUTION AGAINST ESD FOR SEMICONDUCTORS

Note: Strong electric field, when exposed to a MOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it once, when it has occurred. Environmental control must be adequate. When it is dry, humidifier should be used. It is recommended to avoid using insulators that easily build static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work bench and floor should be grounded. The operator should be grounded using wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions need to be taken for PW boards with semiconductor devices on it.

② HANDLING OF UNUSED INPUT PINS FOR CMOS

Note: No connection for CMOS device inputs can be cause of malfunction. If no connection is provided to the input pins, it is possible that an internal input level may be generated due to noise, etc., hence causing malfunction. CMOS device behave differently than Bipolar or NMOS devices. Input levels of CMOS devices must be fixed high or low by using a pull-up or pull-down circuitry. Each unused pin should be connected to V_{DD} or GND with a resistor, if it is considered to have a possibility of being an output pin. All handling related to the unused pins must be judged device by device and related specifications governing the devices.

③ STATUS BEFORE INITIALIZATION OF MOS DEVICES

Note: Power-on does not necessarily define initial status of MOS device. Production process of MOS does not define the initial operation status of the device. Immediately after the power source is turned ON, the devices with reset function have not yet been initialized. Hence, power-on does not guarantee out-pin levels, I/O settings or contents of registers. Device is not initialized until the reset signal is received. Reset operation must be executed immediately after power-on for devices having reset function.

[MEMO]

M4 96.5